

F.E. (All Branches) (CB) (Sem-I)

(2 Hours)

[Total Marks:60]

N.B.: (1) Question. 1 is **compulsory**.(2) Attempt any **three** questions from the remaining questions N0.2 to 6.(3) **Assume** suitable **data** wherever required.(4) **Figures** to the **right** indicate **marks**.1. Attempt any **five** questions from the following-

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- Calculate atomic packing fraction of HCP unit cell.
- Express de-Broglie wavelength in various forms.
- Draw the energy band diagram for p-n junction diode in forward and reverse bias condition.
- Define: persistent current, critical temperature, critical magnetic field.
- What is reverberation time? Explain its formula.
- With the help of diagram state direct and inverse piezoelectric effect.
- The resistivity of intrinsic material at room temperature is 2×10^{-4} Ohm-cm. If the mobility of electron is $6 \text{ m}^2/\text{V-sec}$ and mobility of hole is $0.2 \text{ m}^2/\text{V-sec}$. Calculate its intrinsic carrier density.

2 (a) Arrive at the statement that electron can not survive inside the nucleus.

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An electron has a speed of 300m/s with uncertainty of 0.01% . Find the accuracy in its position.

(b) A sample of semiconductor is placed in, uniform magnetic induction B with sample current I and thickness w then obtain the expression for (a) Hall voltage and (b) Hall coefficient.

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3 (a) With neat diagram of unit cell explain the structure of diamond crystal.

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(b) Explain variation of Fermi level with temperature in n-type semiconductor.

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What is the probability of an electron being thermally excited to the conduction band in Si at 30°C . The band gap energy is 1.12eV ($k=1.38 \times 10^{-23} \text{ J/K}$)

4 (a) Distinguish between Type I and Type II superconductors.

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(b) A class room has dimension of $(20 \times 15 \times 10) \text{ m}^3$; the reverberation time is 3 sec.

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Calculate the total absorption of its surfaces and average coefficient of absorption

(c) How ultrasonic waves are produced using quartz crystal in an oscillator?

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5 (a) Show that for an intrinsic semiconductor, the Fermi level lies half way between conduction and valence band.

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(b) State and explain principle of SQUID and explain its working to determine the strength of magnetic field.

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(c) The lowest energy of an electron trapped in a one dimensional box is

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$3.2 \times 10^{-18} \text{ J}$. Calculate the width of the box. Also calculate the next two energies in eV the particle can have?

6 (a) Define ligancy and critical radius ratio. Calculate critical radius ratio for ligancy 6.

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(b) Obtain one dimensional time dependent Schrodinger equation

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(c) Explain photovoltaic effect and write a note on solar cell.

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